74HC366; 74HCT366

Hex buffer/line driver; 3-state; inverting

Rev. 4 — 4 September 2012

Product data sheet

1. General description

The 74HC366; 74HCT366 is a hex inverter/line driver with 3-state outputs controlled by the output enable inputs (OE1). A HIGH on OEn causes the outputs to assume a high impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

The 74HC366; 74HCT366 is functionally identical to:

• 74HC365; 74HCT365, but has inverted outputs

2. Features and benefits

- Inverting outputs
- Input levels:
 - ◆ For 74HC366: CMOS level
 - ◆ For 74HC366: TTL level
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-F exceeds 2000 V
 - ♦ MM EIA/JESD22-A115-A exceeds 200 V
- Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Multiple package options

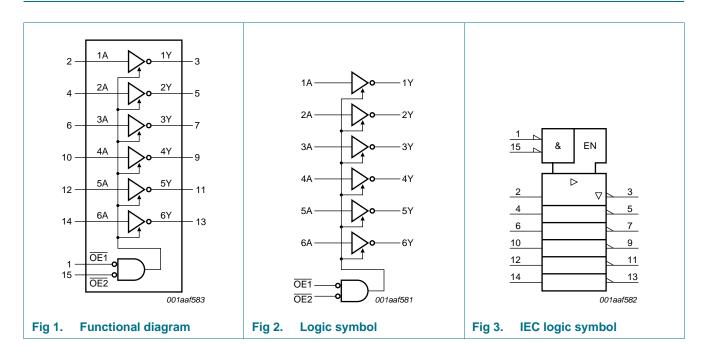


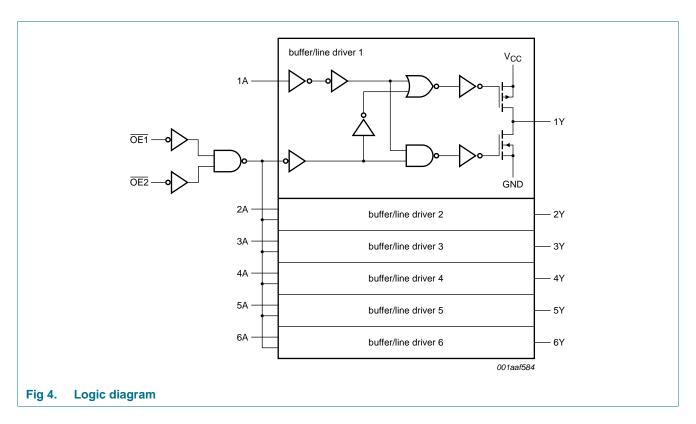
3. Ordering information

Table 1. Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74HC366								
74HC366D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1				
74HC366N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil); long body	SOT38-1				
74HC366PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1				
74HCT366								
74HCT366D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1				
74HCT366DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1				
74HCT366N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil); long body	SOT38-1				
74HCT366PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1				

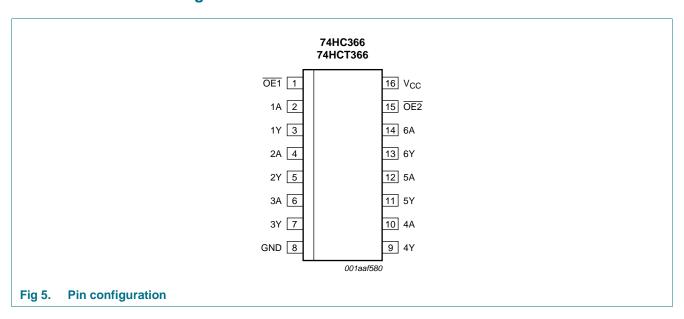
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
OE1	1	output enable input 1 (active LOW)
1A	2	data input 1
1Y	3	data output 1
2A	4	data input 2
2Y	5	data output 2
3A	6	data input 3
3Y	7	data output 3
GND	8	ground (0 V)
4Y	9	data output 4
4A	10	data input 4
5Y	11	data output 5
5A	12	data input 5
6Y	13	data output 6
6A	14	data input 6
OE2	15	output enable input 2 (active LOW)
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table[1]

Control		Input	Output
OE1	OE2	nA	nY
L	L	L	Н
L	L	Н	L
X	Н	X	Z
Н	X	X	Z

^[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care;

Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	-	±20	mA
IO	output current	$V_O = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-	±35	mA
I _{CC}	supply current		-	70	mA
I_{GND}	ground current		-	-70	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	DIP16 package	<u>[1]</u> _	750	mW
		SO16 package	[2] -	500	mW
		SSOP16 package	[3] _	500	mW
		TSSOP16 package	[3] _	500	mW

^[1] For DIP16 packages: P_{tot} derates linearly with 12 mW/K above 70 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	mbol Parameter Conditions			74HC366	3	7	74HCT36	6	Unit
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

^[2] For SO16 packages: Ptot derates linearly with 8 mW/K above 70 °C.

^[3] For SSOP16 and TSSOP16 packages: Ptot derates linearly with 5.5 mW/K above 60 °C.

9. Static characteristics

Table 6. Static characteristics 74HC366

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T _{amb} = 2	5 °C					
V_{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 2.0 \text{ V}$	-	8.0	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}	-	-	-	
		$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	V
		$I_O = -20 \mu A$; $V_{CC} = 4.5 V$	4.4	4.5	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	V
		$I_O = -6.0 \text{ mA}$; $V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 2.0 V$	-	0	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	V
		$I_{O} = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	V
		$I_{O} = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	V
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	μΑ
l _{oz}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.5	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	μΑ
Cı	input capacitance		-	3.5	-	pF
T _{amb} = -	40 °C to +85 °C					
V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0 \text{ V}$	1.5	-	-	V
		$V_{CC} = 4.5 \text{ V}$	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	-	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	-	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	-	-	V
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.84	-	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.34	-	-	V

 Table 6.
 Static characteristics 74HC366 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	-	0.1	V
		$I_{O} = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.33	V
		$I_{O} = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	-	0.33	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$;	-	-	±1.0	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±5.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	80	μΑ
T _{amb} = -	40 °C to +125 °C					
V _{IH} HIGH-level input voltage		$V_{CC} = 2.0 \text{ V}$	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 2.0 \text{ V}$	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	-	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	-	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	-	-	V
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.7	-	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.2	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	-	0.1	V
		$I_{O} = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.4	V
		$I_{O} = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±1.0	μΑ
l _{OZ}	OFF-state output current	V_{I} = V_{IH} or V_{IL} ; V_{O} = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±10.0	μΑ
I _{CC}	supply current	$V_1 = V_{CC}$ or GND; $I_0 = 0$ A; $V_{CC} = 6.0$ V	-	-	160	μΑ

Table 7. Static characteristics 74HCT366

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$T_{amb} = 2$	5 °C					
V_{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V
V_{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
	voltage	$I_O = -20 \mu A$	4.4	4.5	-	V
		$I_{O} = -6.0 \text{ mA}$	3.98	4.32	-	V
74HC_HCT366		All information provided in this document is subject to legal disclaimers.		© NXP E	3.V. 2012. All	ights reserved.

 Table 7.
 Static characteristics 74HCT366 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Parameter	Conditions	Min	Тур	Max	Uni
LOW-level output	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
voltage	I _O = 20 μA	-	0	0.1	V
	$I_{O} = 6.0 \text{ mA}$	-	0.16	0.26	V
input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	μΑ
OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND per input pin; other inputs at GND or V_{CC} ; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	±0.5	μΑ
supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	μΑ
additional supply current	V_{I} = V_{CC} – 2.1 V; other inputs at V_{CC} or GND; I_{O} = 0 A				
	pins nA	-	100	360	μΑ
	pin OE1	-	100	360	μΑ
	pin OE2	-	90	320	μΑ
input capacitance		-	3.5	-	рF
40 °C to +85 °C					
HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	0.8	V
HIGH-level output	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
voltage	$I_0 = -20 \mu A$	4.4	-	-	V
	$I_{O} = -6.0 \text{ mA}$	3.84	-	-	V
LOW-level output	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
voltage	I _O = 20 μA	-	-	0.1	V
	$I_0 = 6.0 \text{ mA}$	-	-	0.33	V
input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±1.0	μΑ
OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND per input pin; other inputs at GND or V_{CC} ; $I_O = 0$ A; $V_{CC} = 5.5$ V			±5.0	μΑ
supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	80	μΑ
additional supply current	$V_I = V_{CC} - 2.1 \text{ V}$; other inputs at V_{CC} or GND; $I_O = 0 \text{ A}$				
	pins nA	-	-	450	μΑ
	pin OE1	-	-	450	μΑ
	pin OE2	-	-	400	μΑ
40 °C to +125 °C					
HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
HIGH-level output	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
voltage	$I_O = -20 \mu A$	4.4	-	-	V
	$I_0 = -6.0 \text{ mA}$	3.7	-	-	V
LOW-level output	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$				
voltage	I _O = 20 μA	-	-	0.1	V
	$I_0 = 6.0 \text{ mA}$	-	-	0.4	V
input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±1.0	μΑ
<u> </u>		-	-	±10.0	μA
	input leakage current OFF-state output current supply current additional supply current additional supply current input capacitance to °C to +85 °C HIGH-level input voltage LOW-level output voltage LOW-level output voltage input leakage current OFF-state output current supply current additional supply current additional supply current to °C to +125 °C HIGH-level input voltage LOW-level input voltage LOW-level input voltage LOW-level output voltage LOW-level output voltage LOW-level output voltage LOW-level output voltage input leakage current	$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$		$ \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	COW-level output voltage Vi = Vin or Vil.; Voc = 4.5 V Vin = Vil. or Vil.; Voc = 4.5 V Vin = Vil. or Vil.; Voc = 5.5 V Vin = Vil. or Vil.; Voc = 5.5 V Vin = Vil. or Vil.; Voc = Voc or GND; Voc = 5.5 V Vin = Vil. or Vil.; Voc = Voc or GND per input pin; other inputs at GND or Voc; Io = 0 A; Voc = 5.5 V Vin = Vil. or Vil.; Voc = Voc or GND; Io = 0 A; Voc = 5.5 V Vin = Vil. or Vil.; Voc = Voc or GND; Io = 0 A; Voc = 5.5 V Vin = Vil. or Vil.

 Table 7.
 Static characteristics 74HCT366 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	160	μΑ
ΔI_{CC}	additional supply current	V_{I} = V_{CC} – 2.1 V; other inputs at V_{CC} or GND; I_{O} = 0 A				
		pins nA	-	-	490	μΑ
		pin OE1	-	-	490	μΑ
		pin OE2	-	-	441	μΑ

10. Dynamic characteristics

Table 8. Dynamic characteristics 74HC366

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; see test circuit Figure 8.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$T_{amb} = 2$	5 ℃					
t _{pd}	propagation delay	nA to nY; see Figure 6	<u>[1]</u>			
		$V_{CC} = 2.0 \text{ V}$	-	33	100	ns
		$V_{CC} = 4.5 \text{ V}$	-	12	20	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	10	-	ns
		$V_{CC} = 6.0 \text{ V}$	-	10	17	ns
t _{en}	enable time	OEn to nY; see Figure 7	[2]			
		V _{CC} = 2.0 V	-	44	150	ns
		V _{CC} = 4.5 V	-	16	30	ns
		$V_{CC} = 6.0 \text{ V}$	-	13	26	ns
t _{dis}	disable time	OEn to nY; see Figure 7	<u>[3]</u>			
		$V_{CC} = 2.0 \text{ V}$	-	55	150	ns
		$V_{CC} = 4.5 \text{ V}$	-	20	30	ns
		$V_{CC} = 6.0 \text{ V}$	-	16	26	ns
t _t	transition time	see Figure 6	[4]			
		$V_{CC} = 2.0 \text{ V}$	-	14	60	ns
		V _{CC} = 4.5 V	-	5	12	ns
		V _{CC} = 6.0 V	-	4	10	ns
C_{PD}	power dissipation capacitance	per buffer; $V_I = GND$ to V_{CC}	<u>[5]</u> -	30	-	pF
T _{amb} = -	40 °C to +85 °C					
t _{pd}	propagation delay	nA to nY; see Figure 6	[1]			
		$V_{CC} = 2.0 \text{ V}$	-	-	125	ns
		V _{CC} = 4.5 V	-	-	25	ns
		V _{CC} = 6.0 V	-	-	21	ns
t _{en}	enable time	OEn to nY; see Figure 7	[2]			
		V _{CC} = 2.0 V	-	-	190	ns
		V _{CC} = 4.5 V	-	-	38	ns
		V _{CC} = 6.0 V	-	-	33	ns

Table 8. Dynamic characteristics 74HC366 ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \ pF$ unless otherwise specified; see test circuit Figure 8.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{dis}	disable time	OEn to nY; see Figure 7	<u>[3]</u>			
		V _{CC} = 2.0 V	-	-	190	ns
		V _{CC} = 4.5 V	-	-	38	ns
		V _{CC} = 6.0 V	-	-	33	ns
t _t	transition time	see <u>Figure 6</u>	<u>[4]</u>			
		V _{CC} = 2.0 V	-	-	75	ns
		V _{CC} = 4.5 V	-	-	15	ns
		V _{CC} = 6.0 V	-	-	13	ns
T _{amb} = -	40 °C to +125 °C					
t _{pd}	propagation delay	nA to nY; see Figure 6	[1]			
		V _{CC} = 2.0 V	-	-	150	ns
		V _{CC} = 4.5 V	-	-	30	ns
		V _{CC} = 6.0 V	-	-	26	ns
t _{en}	enable time	OEn to nY; see Figure 7	[2]			
		V _{CC} = 2.0 V	-	-	225	ns
		V _{CC} = 4.5 V	-	-	45	ns
		V _{CC} = 6.0 V	-	-	38	ns
t _{dis}	disable time	OEn to nY; see Figure 7	[3]			
		V _{CC} = 2.0 V	-	-	225	ns
		V _{CC} = 4.5 V	-	-	45	ns
		V _{CC} = 6.0 V	-	-	38	ns
t _t	transition time	see Figure 6	<u>[4]</u>			
		V _{CC} = 2.0 V	-	-	90	ns
		V _{CC} = 4.5 V	-	-	18	ns
		V _{CC} = 6.0 V	-	-	15	ns

^[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \sum (C_L \times V_{CC}{}^2 \times f_o)$$
 where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs.}$

^[2] t_{en} is the same as t_{PZH} and t_{PZL} .

^[3] t_{dis} is the same as t_{PHZ} and t_{PLZ} .

^[4] t_t is the same as t_{THL} and t_{TLH} .

 Table 9.
 Dynamic characteristics 74HCT366

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; see test circuit Figure 8.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
t _{pd}	propagation delay	nA to nY; see Figure 6	[1]			
		V _{CC} = 4.5 V	-	13	24	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	11	-	ns
t _{en}	enable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[2] _	16	35	ns
t _{dis}	disable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[3]	20	35	ns
t _t	transition time	V _{CC} = 4.5 V; see <u>Figure 6</u>	[4] _	5	12	ns
C_{PD}	power dissipation capacitance	per buffer; $V_I = GND$ to $(V_{CC} - 1.5 V)$	[5] _	30	-	pF
T _{amb} = -	40 °C to +85 °C					
t _{pd}	propagation delay	nA to nY; V _{CC} = 4.5 V; see Figure 6	<u>[1]</u> -	-	30	ns
t _{en}	enable time	$\overline{\text{OEn}}$ to nY; $V_{CC} = 4.5 \text{ V}$; see $\overline{\text{Figure 7}}$	[2] _	-	44	ns
t _{dis}	disable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[3] _	-	44	ns
t _t	transition time	V _{CC} = 4.5 V; see <u>Figure 6</u>	[4] -	-	15	ns
T _{amb} = -	40 °C to +125 °C					
t _{pd}	propagation delay	nA to nY; V _{CC} = 4.5 V; see Figure 6	<u>[1]</u> -	-	36	ns
t _{en}	enable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[2] _	-	53	ns
t _{dis}	disable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[3] _	-	53	ns
t _t	transition time	V _{CC} = 4.5 V; see <u>Figure 6</u>	[4] _	-	18	ns

^[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

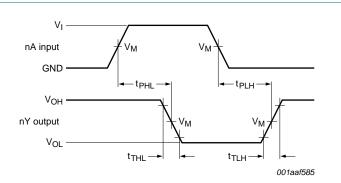
 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$

^[2] t_{en} is the same as t_{PZH} and t_{PZL} .

^[3] t_{dis} is the same as t_{PHZ} and t_{PLZ} .

^[4] t_t is the same as t_{THL} and t_{TLH} .

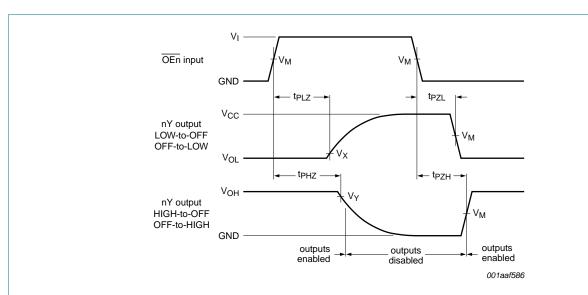
11. Waveforms



Measurement points are given in Table 10.

 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. Propagation delay data input (nA) to output (nY) and output transition time



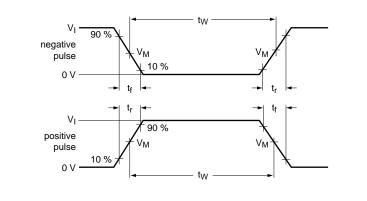
Measurement points are given in Table 10.

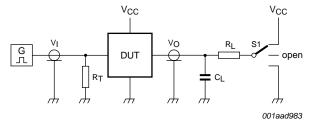
 $\ensuremath{V_{OL}}$ and $\ensuremath{V_{OH}}$ are typical output voltage levels that occur with the output load.

Fig 7. 3-state enable and disable times

Table 10. Measurement points

Туре	Input	Output						
	V _M	V _M	V _X	V _Y				
74HC366	0.5V _{CC}	0.5V _{CC}	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$				
74HCT366	1.3 V	1.3 V	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$				





Test data is given in Table 11.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator

C_L = Load capacitance including jig and probe capacitance

R_L = Load resistor

S1 = Test selection switch

Fig 8. Load circuitry for measuring switching times

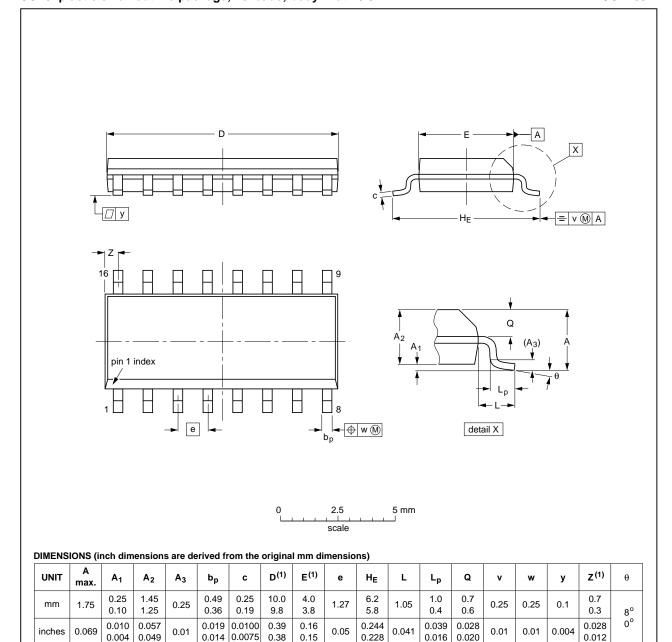
Table 11. Test data

Туре	Input		Load		S1 position				
	VI	t _r , t _f	C _L	R _L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}		
74HC366	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}		
74HCT366	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}		

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

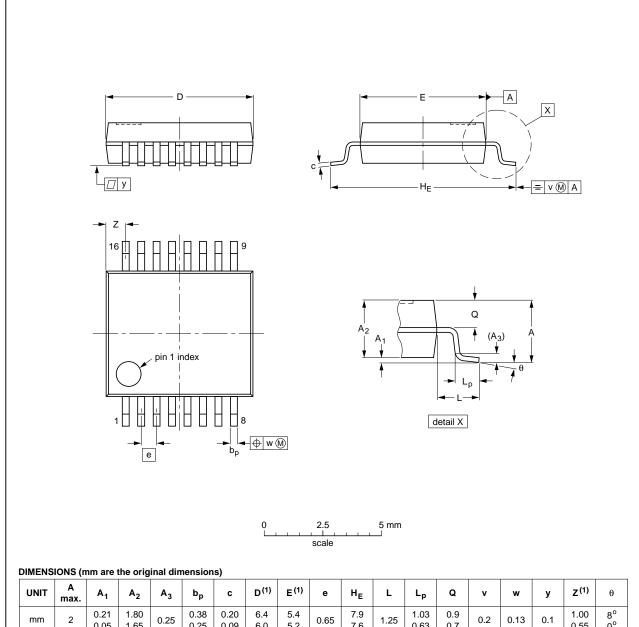
				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT109-1	076E07	MS-012			99-12-27 03-02-19

Fig 9. Package outline SOT109-1 (SO16)

74HC_HCT366

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT338-1		MO-150				99-12-27 03-02-19	

Fig 10. Package outline SOT338-1 (SSOP16)

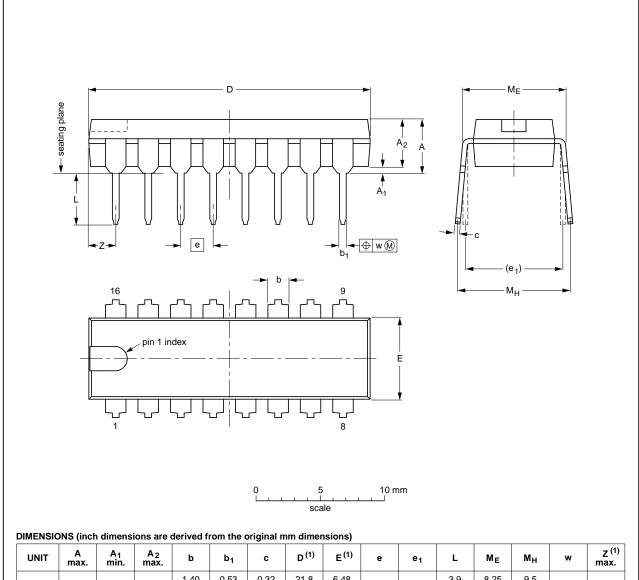
74HC_HCT366

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DIP16: plastic dual in-line package; 16 leads (300 mil); long body

SOT38-1



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.7	0.51	3.7	1.40 1.14	0.53 0.38	0.32 0.23	21.8 21.4	6.48 6.20	2.54	7.62	3.9 3.4	8.25 7.80	9.5 8.3	0.254	2.2
inches	0.19	0.02	0.15	0.055 0.045	0.021 0.015	0.013 0.009	0.86 0.84	0.26 0.24	0.1	0.3	0.15 0.13	0.32 0.31	0.37 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

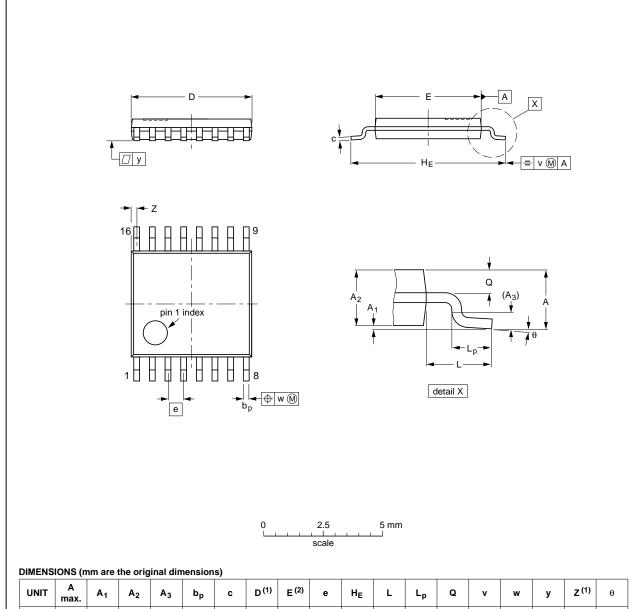
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT38-1	050G09	MO-001	SC-503-16			99-12-27 03-02-13
					—	03

Fig 11. Package outline SOT38-1 (DIP16)

74HC_HCT366

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



-		······································																	
	UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E (2)	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
	mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT403-1		MO-153			99-12-27 03-02-18

Fig 12. Package outline SOT403-1 (TSSOP16)

74HC_HCT366

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13. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT366 v.4	20120904	Product data sheet	-	74HC_HCT366 v.3
Modifications:	 Legal pages 	updated.		
74HC_HCT366 v.3	20061121	Product data sheet	-	74HC_HCT366_CNV v.2
74HC_HCT366_CNV v.2	19901201	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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74HC366; 74HCT366

Hex buffer/line driver; 3-state; inverting

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